



ON Semiconductor®

# FDMS86350

## N-Channel PowerTrench® MOSFET 80 V, 130 A, 2.4 mΩ

### Features

- Max  $r_{DS(on)}$  = 2.4 mΩ at  $V_{GS} = 10\text{ V}$ ,  $I_D = 25\text{ A}$
- Max  $r_{DS(on)}$  = 3.2 mΩ at  $V_{GS} = 8\text{ V}$ ,  $I_D = 22\text{ A}$
- Advanced Package and Silicon combination for low  $r_{DS(on)}$  and high efficiency
- MSL1 robust package design
- 100% UIL tested
- RoHS Compliant

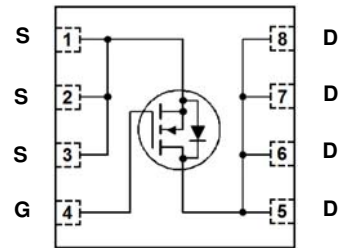
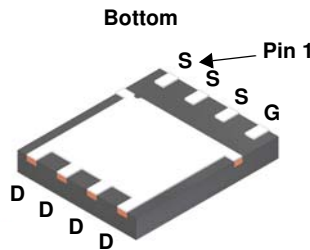
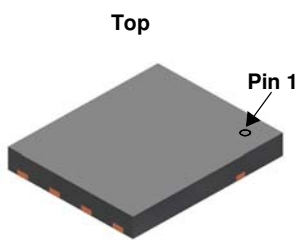


### General Description

This N-Channel MOSFET is produced using ON Semiconductor's advanced Power Trench® process that has been especially tailored to minimize the on-state resistance and yet maintain superior switching performance.

### Applications

- Primary MOSFET
- Synchronous Rectifier
- Load Switch
- Motor Control Switch



Power 56

### MOSFET Maximum Ratings $T_A = 25\text{ °C}$ unless otherwise noted

Symbol	Parameter	Rated	Units
$V_{DS}$	Drain to Source Voltage	80	V
$V_{GS}$	Gate to Source Voltage	±20	V
$I_D$	Drain Current -Continuous	$T_C = 25\text{ °C}$	A
	-Continuous	$T_A = 25\text{ °C}$ (Note 1a)	
	-Pulsed	(Note 4)	
$E_{AS}$	Single Pulse Avalanche Energy	(Note 3)	mJ
$P_D$	Power Dissipation	$T_C = 25\text{ °C}$	W
	Power Dissipation	$T_A = 25\text{ °C}$ (Note 1a)	
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to +150	°C

### Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	0.8	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	45	

### Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMS86350	FDMS86350	Power 56	13 "	12 mm	3000 units

## Electrical Characteristics $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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### Off Characteristics

$BV_{DSS}$	Drain to Source Breakdown Voltage	$I_D = 250\text{ }\mu\text{A}$ , $V_{GS} = 0\text{ V}$	80			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$ , referenced to $25\text{ }^\circ\text{C}$		45		mV/ $^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 64\text{ V}$ , $V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
$I_{GSS}$	Gate to Source Leakage Current	$V_{GS} = \pm 20\text{ V}$ , $V_{DS} = 0\text{ V}$			$\pm 100$	nA

### On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$ , $I_D = 250\text{ }\mu\text{A}$	2.5	3.8	4.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$ , referenced to $25\text{ }^\circ\text{C}$		-12		mV/ $^\circ\text{C}$
$r_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\text{ V}$ , $I_D = 25\text{ A}$		2.0	2.4	m $\Omega$
		$V_{GS} = 8\text{ V}$ , $I_D = 22\text{ A}$		2.5	3.2	
		$V_{GS} = 10\text{ V}$ , $I_D = 25\text{ A}$ , $T_J = 125\text{ }^\circ\text{C}$		3.1	3.8	
$g_{FS}$	Forward Transconductance	$V_{DS} = 5\text{ V}$ , $I_D = 25\text{ A}$		70		S

### Dynamic Characteristics

$C_{iss}$	Input Capacitance	$V_{DS} = 40\text{ V}$ , $V_{GS} = 0\text{ V}$ , $f = 1\text{ MHz}$		8030	10680	pF
$C_{oss}$	Output Capacitance			1370	1825	pF
$C_{rss}$	Reverse Transfer Capacitance			31	50	pF
$R_g$	Gate Resistance		0.1	1.1	3	$\Omega$

### Switching Characteristics

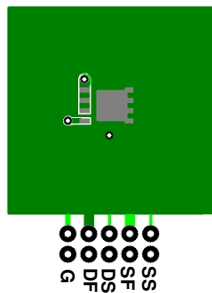
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 40\text{ V}$ , $I_D = 25\text{ A}$ , $V_{GS} = 10\text{ V}$ , $R_{GEN} = 6\text{ }\Omega$		50	80	ns
$t_r$	Rise Time			34	55	ns
$t_{d(off)}$	Turn-Off Delay Time			40	65	ns
$t_f$	Fall Time			11	20	ns
$Q_g$	Total Gate Charge	$V_{GS} = 0\text{ V to } 10\text{ V}$	$V_{DD} = 40\text{ V}$ , $I_D = 25\text{ A}$	110	155	nC
$Q_g$	Total Gate Charge	$V_{GS} = 0\text{ V to } 8\text{ V}$		90	127	nC
$Q_{gs}$	Gate to Source Charge			46		nC
$Q_{gd}$	Gate to Drain "Miller" Charge			23		nC

### Drain-Source Diode Characteristics

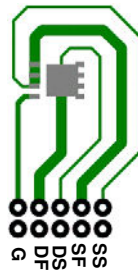
$I_S$	Diode Continuous Forward Current	$T_C = 25\text{ }^\circ\text{C}$			130	A
$I_{S, pulse}$	Diode Pulse Current	$T_C = 25\text{ }^\circ\text{C}$			300	A
$V_{SD}$	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{ V}$ , $I_S = 2.1\text{ A}$ (Note 2)		0.71	1.2	V
		$V_{GS} = 0\text{ V}$ , $I_S = 25\text{ A}$ (Note 2)		0.79	1.3	
$t_{rr}$	Reverse Recovery Time	$I_F = 25\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$		63	101	ns
$Q_{rr}$	Reverse Recovery Charge			62	100	nC

#### Notes:

- $R_{\theta JA}$  is determined with the device mounted on a  $1\text{ in}^2$  pad 2 oz copper pad on a  $1.5 \times 1.5\text{ in.}$  board of FR-4 material.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.



a.  $45\text{ }^\circ\text{C}/\text{W}$  when mounted on a  $1\text{ in}^2$  pad of 2 oz copper.



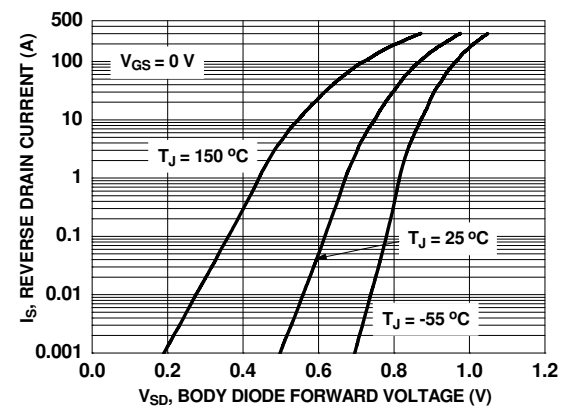
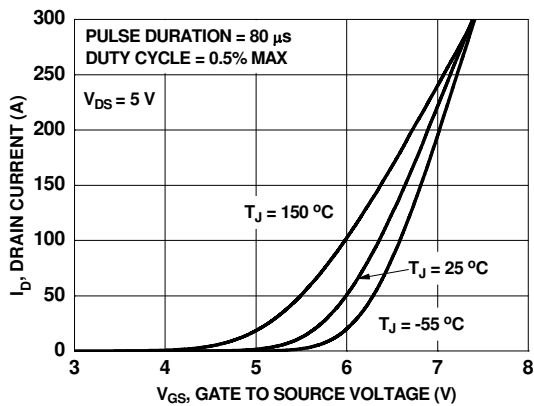
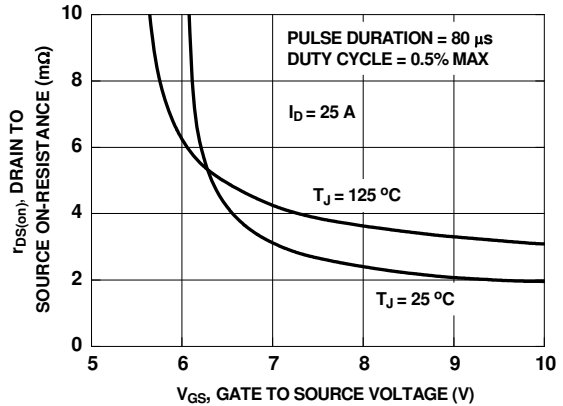
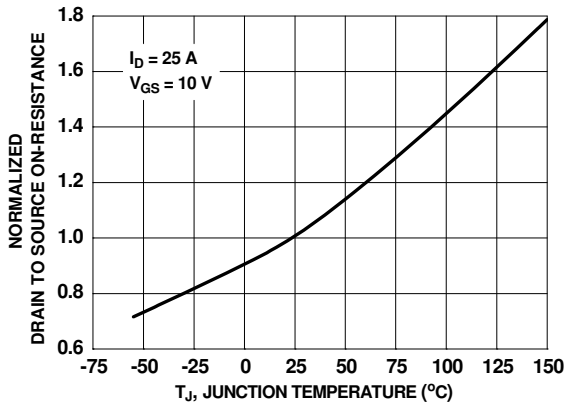
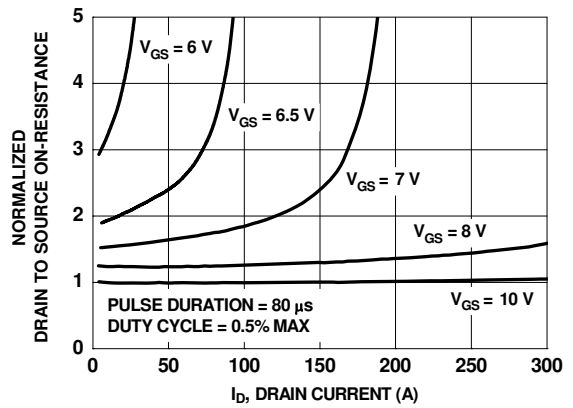
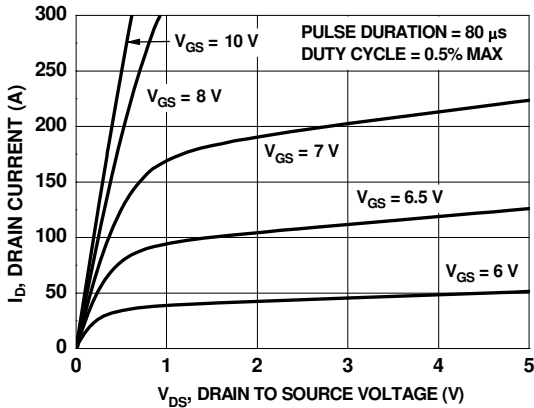
b.  $115\text{ }^\circ\text{C}/\text{W}$  when mounted on a minimum pad of 2 oz copper.

- Pulse Test: Pulse Width <  $300\text{ }\mu\text{s}$ , Duty cycle < 2.0%.

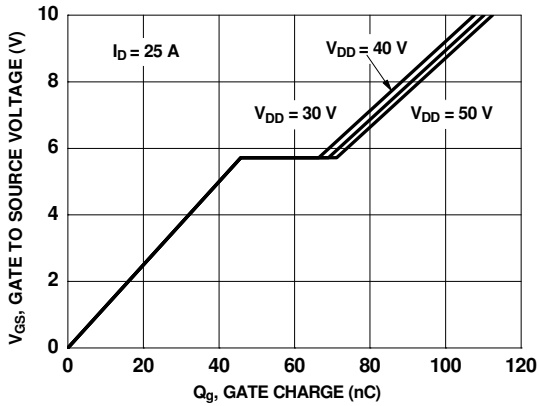
- $E_{AS}$  of 864 mJ is based on starting  $T_J = 25\text{ }^\circ\text{C}$ ,  $L = 3\text{ mH}$ ,  $I_{AS} = 24\text{ A}$ ,  $V_{DD} = 80\text{ V}$ ,  $V_{GS} = 10\text{ V}$ , 100% test at  $L = 0.1\text{ mH}$ ,  $I_{AS} = 74\text{ A}$ .

- Pulse  $I_d$  limited by junction temperature,  $t_d \leq 100\text{ }\mu\text{s}$ , please refer to SOA curve for more details.

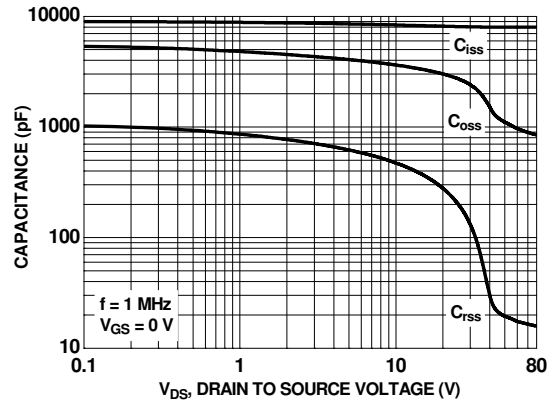
**Typical Characteristics**  $T_J = 25\text{ }^\circ\text{C}$  unless otherwise noted



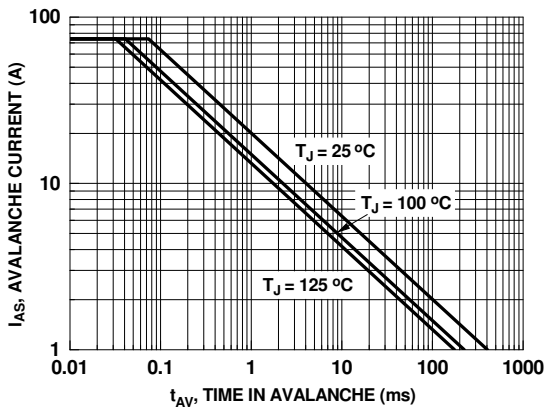
**Typical Characteristics**  $T_J = 25\text{ }^\circ\text{C}$  unless otherwise noted



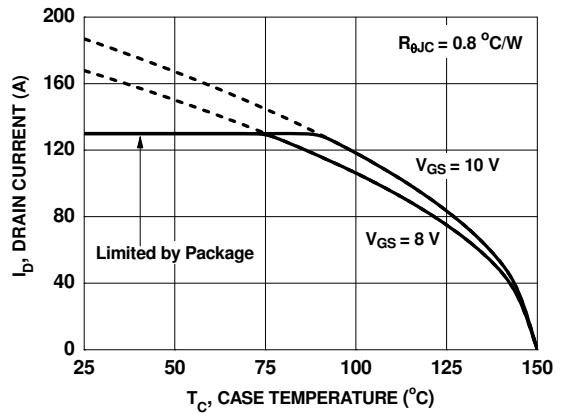
**Figure 7. Gate Charge Characteristics**



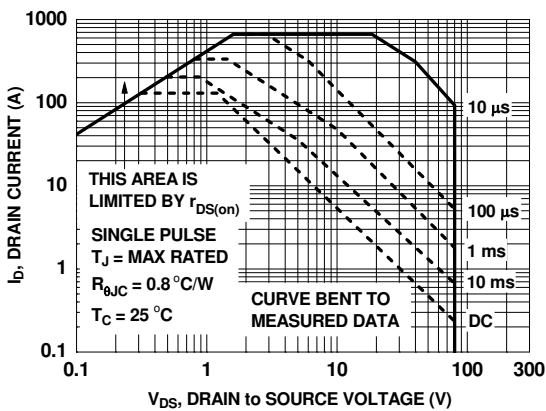
**Figure 8. Capacitance vs Drain to Source Voltage**



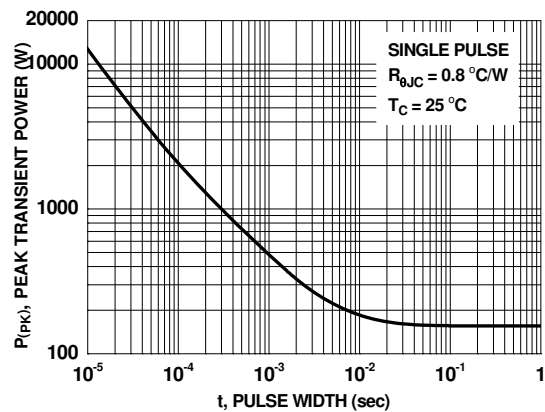
**Figure 9. Unclamped Inductive Switching Capability**



**Figure 10. Maximum Continuous Drain Current vs Case Temperature**

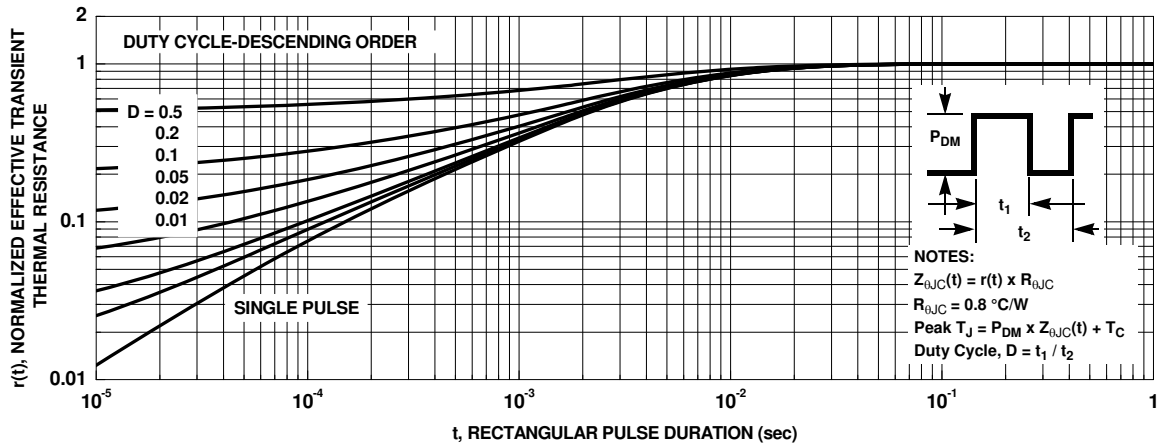


**Figure 11. Forward Bias Safe Operating Area**




**Figure 12. Single Pulse Maximum Power Dissipation**

**Typical Characteristics**  $T_J = 25\text{ }^\circ\text{C}$  unless otherwise noted



**Figure 13. Junction-to-Case Transient Thermal Response Curve**

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